FUJI ELECTRIC

2SK2018-01L,S

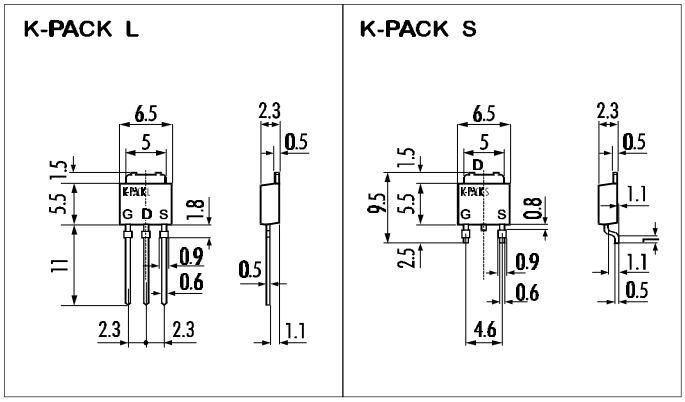
FAP-III Series

N-channel MOS-FET			
60V	0,1Ω	10A	20W

> Features

- High Current
- Low On-Resistance
- No Secondary Breakdown
- Low Driving Power
- High Forward Transconductance
- Avalanche Proof

> Outline Drawing



> Applications

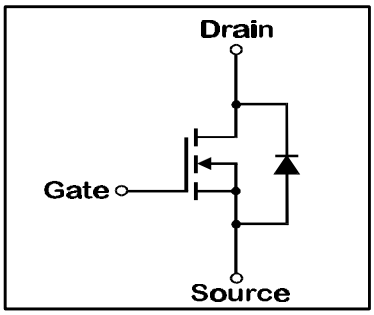
- Motor Control
- General Purpose Power Amplifier
- DC-DC converters

> Maximum Ratings and Characteristics

- Absolute Maximum Ratings (T_C=25°C), unless otherwise specified

Item	Symbol	Rating	Unit
Drain-Source-Voltage	V_{DS}	60	V
Drain-Gate-Voltage(R_{GS}=20KΩ)	V_{DGR}	60	V
Continous Drain Current	I_D	10	A
Pulsed Drain Current	$I_{D(puls)}$	40	A
Gate-Source-Voltage	V_{GS}	±20	V
Max. Power Dissipation	P_D	20	W
Operating and Storage Temperature Range	T_{ch}	150	°C
	T_{stg}	-55 ~ +150	°C

> Equivalent Circuit



- Electrical Characteristics (T_C=25°C), unless otherwise specified

Item	Symbol	Test conditions		Min.	Typ.	Max.	Unit
Drain-Source Breakdown-Voltage	$V_{(BR)DSS}$	I_D=1mA	V_{GS}=0V	60			V
Gate Threshhold Voltage	$V_{GS(th)}$	I_D=1mA	V_{DS}=V_{GS}	1,0	1,5	2,5	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V	T_{ch}=25°C		10	500	µA
		V_{GS}=0V	T_{ch}=125°C		0,2	1,0	mA
Gate Source Leakage Current	I_{GSS}	V_{GS}=±20V	V_{DS}=0V		10	100	nA
Drain Source On-State Resistance	$R_{DS(on)}$	I_D=5A	V_{GS}=4V		0,11	0,16	Ω
		I_D=5A	V_{GS}=10V		0,07	0,1	Ω
Forward Transconductance	g_{fs}	I_D=5A	V_{DS}=25V	4	8		S
Input Capacitance	C_{iss}	V_{DS}=25V			500	750	pF
Output Capacitance	C_{oss}	V_{GS}=0V			200	300	pF
Reverse Transfer Capacitance	C_{rss}	f=1MHz			80	120	pF
Turn-On-Time t_{on} (t_{on}=$t_{d(on)}$+t_r)	$t_{d(on)}$	V_{CC}=30V			10	15	ns
	t_r	I_D=5A			20	30	ns
Turn-Off-Time t_{off} (t_{on}=$t_{d(off)}$+t_f)	$t_{d(off)}$	V_{GS}=10V			100	150	ns
	t_f	R_{GS}=25Ω			50	75	ns
Avalanche Capability	I_{AV}	L=100µH	T_{ch}=25°C	10			A
Continous Reverse Drain Current	I_{DR}					10	A
Pulsed Reverse Drain Current	I_{DRM}					40	A
Diode Forward On-Voltage	V_{SD}	I_F=2xI_{DR}	V_{GS}=0V T_{ch}=25°C		1,2		V
Reverse Recovery Time	t_{rr}	I_F=I_{DR}	V_{GS}=0V		100		ns
Reverse Recovery Charge	Q_{rr}	-dI_F/dt=100A/µs	T_{ch}=25°C		0,15		µC

- Thermal Characteristics

Item	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Thermal Resistance	$R_{th(ch-a)}$	channel to air				°C/W
	$R_{th(ch-c)}$	channel to case			6,25	°C/W

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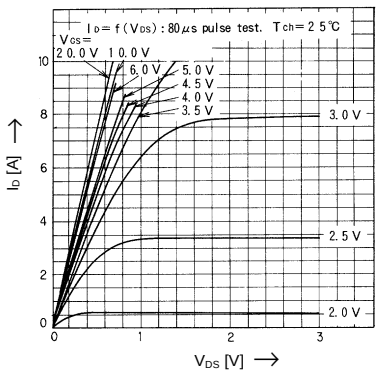
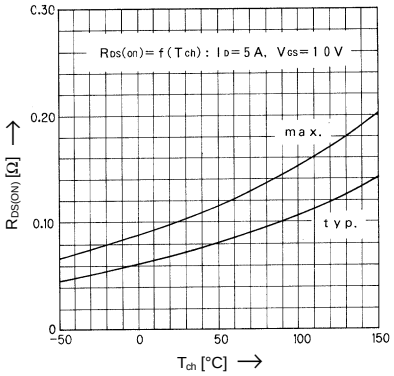
> Characteristics

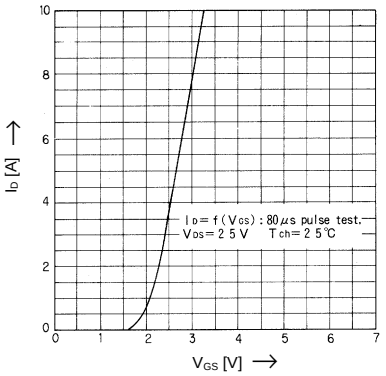
Typical Output Characteristics



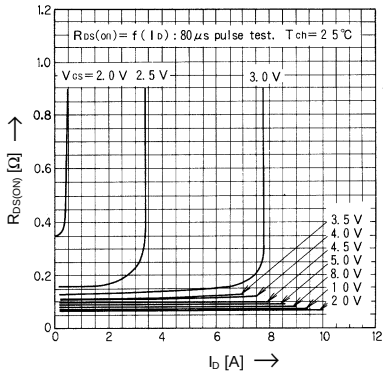
Drain-Source-On-State Resistance vs. T_{ch}



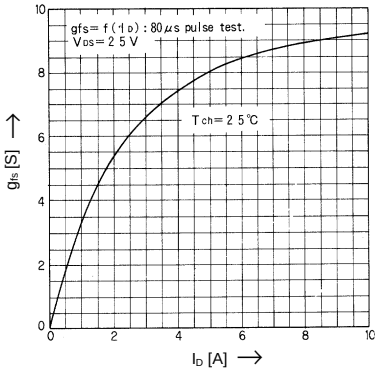
Typical Transfer Characteristics



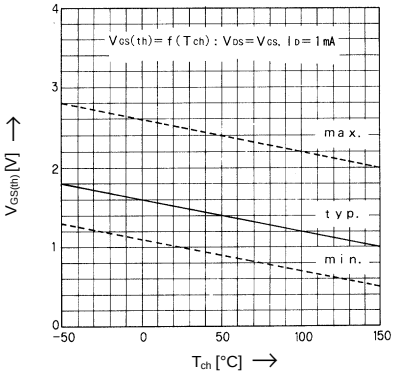
Typical Drain-Source-On-State-Resistance vs. I_D



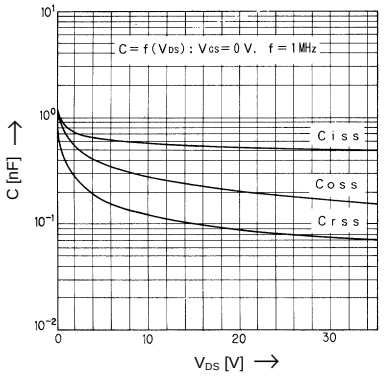
Typical Forward Transconductance vs. I_D



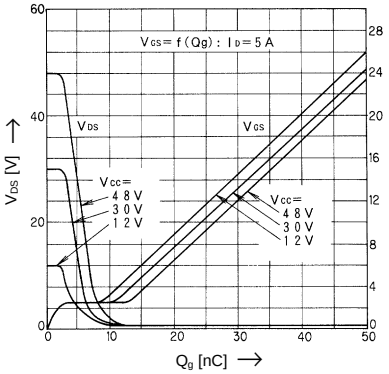
Gate Threshold Voltage vs. T_{ch}



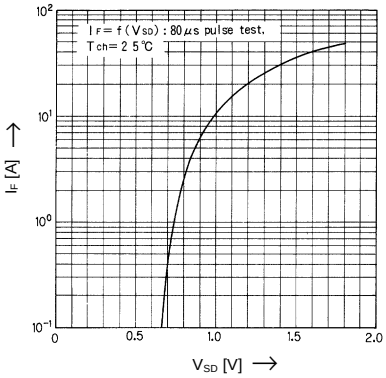
Typical Capacitance vs. V_{DS}



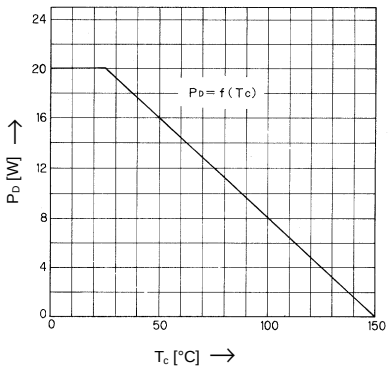
Typical Input Charge



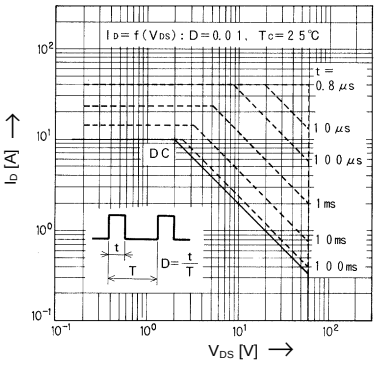
Forward Characteristics of Reverse Diode



Allowable Power Dissipation vs. T_C



Safe operation area



Transient Thermal impedance